N-Channel Silicon MOSFET



2SK2910

Ultrahigh-Speed Switching Applications

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- \cdot 4V drive.

Package Dimensions

unit:mm

Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		30	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	۱ _D		0.8	A
Drain Current (Pulse)	I _{DP}	PW≤10µs, duty cycle≤1%	3.2	A
Allowable Power Dissipation	PD		0.25	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V _(BR) DSS	I _D =1mA, V _{GS} =0	30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =30V, V _{GS} =0			10	μA
Gate-to-Source Leakage Current	IGSS	$V_{GS}=\pm 16V, V_{DS}=0$			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	1.0		2.4	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =400mA	0.5	1.6		S
Static Drain-to-Source On-State Resistance	R _{DS(on)} 1	I _D =400mA, V _{GS} =10V		230	300	mΩ
	R _{DS(on)} 2	I _D =400mA, V _{GS} =4V		350	480	mΩ

Marking : EK

Continued on next page.

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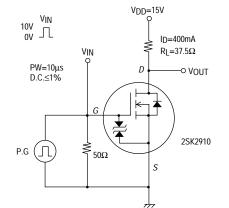
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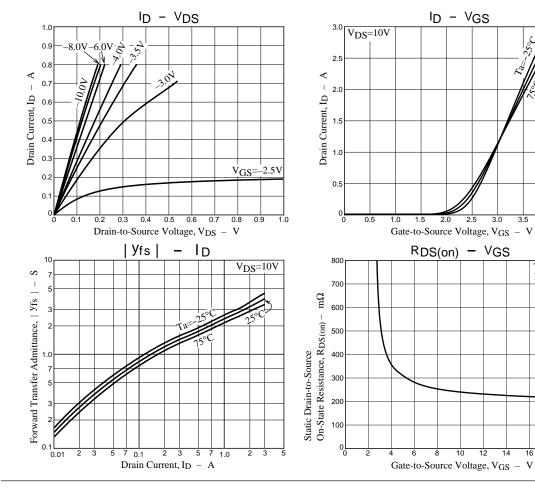
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Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Input Capacitance	Ciss	V _{DS} =10V, f=1MHz		90		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		50		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		22		pF
Turn-ON Delay Time	^t d(on)	See specified Test Circuit		10		ns
Rise Time	tr	See specified Test Circuit		10		ns
Turn-OFF Delay Time	^t d(off)	See specified Test Circuit		30		ns
Fall Time	t _f	See specified Test Circuit		15		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =800mA		5		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =800mA		1		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =800mA		1		nC
Diode Forward Voltage	V _{SD}	I _S =800mA, V _{GS} =0		1.0	1.2	V

Switching Time Test Circuit

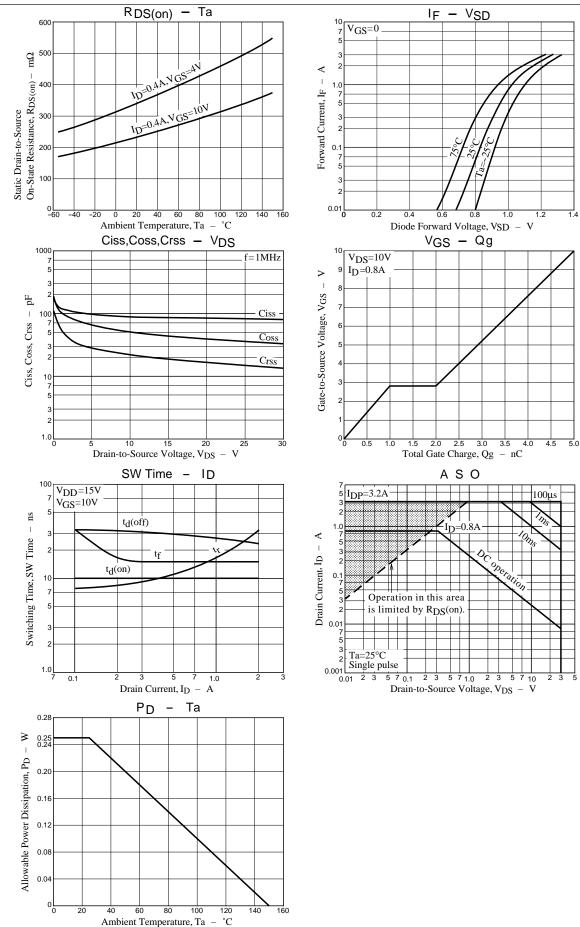




16 18 20

4.0 4.5

Ta=25°C I_D=0.4A



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